

**IN THE CLAIMS:**

Please cancel claims 4, 5, 21, and 22 without prejudice. This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (currently amended): A high frequency semiconductor device comprising:  
a semiconductor substrate;  
at least one active element formed on said semiconductor substrate;  
a ground plate connected to a ground potential, said ground plate being provided ~~above~~ ~~said active element~~ on said semiconductor substrate;  
at least one insulating interlayer;  
a plurality of line conductors provided ~~above~~ on said ground plate, with said at least one insulating interlayer provided therebetween; the plurality of line conductors individually acting as a microstrip line combining with said ground plate;  
at least one terminal for connecting to the exterior; and  
a shield plate provided ~~above~~ on a highest layer of the plurality of line conductors, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential and ~~covering the plurality of line conductors~~ substantially covering the entirety of said semiconductor substrate except for an area of said at least one terminal.

Claim 2 (original): A high frequency semiconductor device according to Claim 1, wherein said at least one terminal is a wire-bonding pad.

Claim 3 (currently amended): A high frequency semiconductor device according to Claim 2, wherein said shield plate has an opening in an area in which the said wire-bonding pad is positioned.

Claim 4 (canceled)

Claim 5 (canceled)

Claim 6 (currently amended): A high frequency semiconductor device according to Claim 1, further comprising:

a plurality of throughholes formed in the periphery of said a shield plate so as to surround an inner area excluding the periphery, the throughholes reaching said a ground plate; and internal conductors provided in the throughholes, said internal conductors connecting said a shield plate and said a ground plate.

Claim 7 (canceled)

Claim 8 (original): A high frequency semiconductor device according to Claim 1, wherein said at least one terminal is connected to the first major surface of said semiconductor substrate by a viahole penetrating said semiconductor substrate.

Claim 9 (currently amended): A high frequency semiconductor device according to Claim 7 25, wherein said at least one terminal is a flip chip pad.

Claim 10 (original): A high frequency semiconductor device according to Claim 1, wherein:  
said semiconductor substrate is divided into an element-arranged area in which  
semiconductor elements are formed and an outer area around said element-arranged area in which  
at least one terminal is provided; and  
said shield plate selectively covers said element-arranged area.

Claim 11 (original): A high frequency semiconductor device according to Claim 10, wherein  
further comprising:

a plurality of throughholes formed in the periphery of said shield plate so as to surround an  
inner area excluding the periphery, the throughholes reaching said ground plate; and  
internal conductors provided in the throughholes, said internal conductors connecting said  
shield plate and said ground plate;

wherein said at least one terminal and said element-arranged area are made in conduction by  
an area in which the throughholes are not provided.

Claim 12 (original): A high frequency semiconductor device according to Claim 1, wherein  
said terminal is an antenna.

Claim 13 (original): A high frequency semiconductor device according to Claim 12, wherein  
said shield plate has an opening in a portion corresponding to said antenna.

Claim 14 (original): A high frequency semiconductor device according to Claim 12, wherein  
a terminal for electrically connecting to the exterior is further provided on the back of said  
semiconductor substrate.

Claim 15 (original): A high frequency semiconductor device according to Claim 14, wherein said terminal is connected to the surface of said semiconductor substrate by a viahole penetrating said semiconductor substrate.

Claim 16 (previously presented): A high frequency semiconductor device according to Claim 14, wherein said terminal is a flip chip bonding electrode.

Claim 17 (original): A high frequency semiconductor device according to Claim 12, wherein said ground plate is used as an antenna grand plane in said antenna.

Claim 18 (original): A high frequency semiconductor device according to Claim 12, wherein said antenna is provided on said shield plate, and said shield plate is used as an antenna grand plane.

Claim 19 (original): A high frequency semiconductor device according to Claim 12, wherein said antenna is a patch antenna.

Claim 20 (original): A high frequency semiconductor device according to Claim 1, wherein said at least one insulating interlayer is made of one of polyimide and benzocyclobutene.

Claim 21 (canceled)

Claim 22 (canceled)

Claim 23 (currently amended): A high frequency semiconductor device comprising:

a semiconductor substrate;

a ground plate connected to ~~the~~ a ground potential;

at least one insulating interlayer;

a plurality of line conductor conductors provided above on said ground plate, with said at least one insulating interlayer provided therebetween;

at least one terminal for connecting to the exterior; and

a shield plate provided ~~above the~~ on a highest layer of the plurality of line conductor conductors, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential;

wherein said terminal is a patch antenna.

Claim 24 (currently amended): A high frequency semiconductor device comprising:

a semiconductor substrate;

a ground plate connected to ~~the~~ a ground potential;

at least one insulating interlayer;

a plurality of line conductor conductors provided above said ground plate, with said at least one insulating interlayer provided therebetween;

at least one terminal for connecting to the exterior; and

a shield plate provided ~~above the~~ on a highest layer of the plurality of line conductor conductors, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential;

wherein said at least one insulating interlayer is made of one of polyimide and benzocyclobutene.

Claim 25 (New): A high frequency semiconductor device comprising:

a semiconductor substrate having first and second major surfaces;

at least one active element formed on said first major surface of said semiconductor substrate;

a ground plate connected to a ground potential, said ground plate being provided on said first major surface;

at least one insulating interlayer;

a plurality of line conductors provided on said ground plate, with said at least one insulating interlayer provided therebetween, the plurality of line conductors individually acting as a microstrip line combining with said ground plate;

at least one terminal for connecting to the exterior, and

a shield plate provided on a highest layer of the plurality of line conductors, with said at least one insulating interlayer provided therebetween, said shield plate being connected to the ground potential and substantially covering the entirety of said semiconductor substrate, wherein said at least one terminal is formed on said second major surface of said semiconductor substrate.